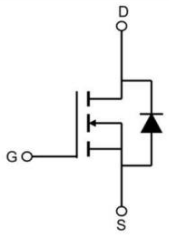
AP5N50K

N-Channel Enhancement Mosfet

DATA SHEET

Features

- 500V,5A
  $R_{DS(ON)}$ <1.5Ω@V_{GS}=10V TYP:1.25Ω
- Fast Switching
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram



Marking and pin assignment

Applications

- PWM applications
- Load Switch
- Power management

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
5N50K	AP5N50K	TO-252	-	-	2500

ABSOLUTE MAXIMUM RATINGS (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current (Tc=25℃) (1)	I_D	5	A
Continuous Drain Current (Tc=100℃)	I_D	3	A
Pulsed Drain Current (1)	I_{DM}	20	A
Drain Power Dissipation	P_D	54	W
Single Pulsed Avalanche Energy (2)	E_{AS}	88	mJ
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2.13	℃/W
Junction Temperature	T_J	-55~ +150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

Notes:

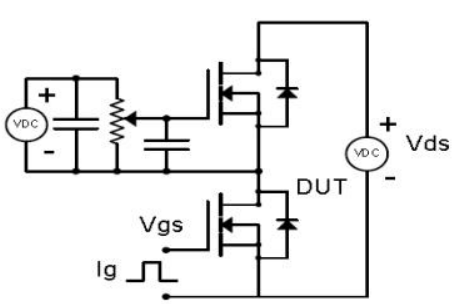
1) Repetitive Rating: pulse width limited by maximum junction temperature
2) EAS condition : T_J=25℃, V_{DD}=50V, V_G=10V, L=5mH, R_g=25Ω, I_{AS}=5.9A

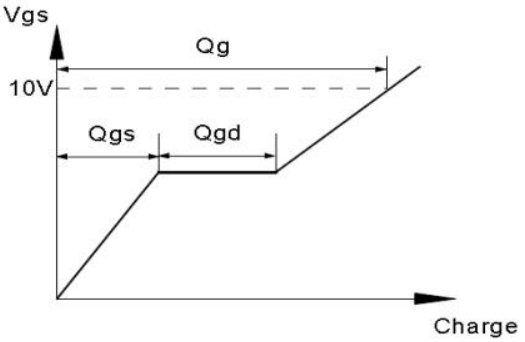
MOSFET ELECTRICAL CHARACTERISTICS(T_J=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	500	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} =500V, V_{GS} = 0V	-	-	1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±30V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	2.0	3.3	4.0	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =2.5A	-	1.25	1.5	Ω
Forward tranconductance	g_{FS}	V_{DS} =10V,I_D=0.25A	1	-	-	S
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =25V, VGS=0V, f=1MHz	-	650	-	pF
Output Capacitance	C_{oss}		-	57	-	
Reverse Transfer Capacitance	C_{rss}		-	13	-	
Switching characteristics						
Turn-off delay time	$t_{d(off)}$	V_{DD}=250V, I_D=5A, R_G=25Ω, V_{GS}=10V	-	20	-	nS
Total Gate Charge	Qg	V_{DS}=400V, I_D=5A, V_{GS}=10V	-	26	-	nC
Gate-Source Charge	Qgs		-	4	-	
Gate-Drain Charge	Qgd		-	15	-	
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	T_J=25℃, V_{GS} =0V, I_S=20A	-	-	1.4	V
Diode Forward current	I_S	T_C=25℃	-	-	5	A
Body Diode Reverse Recovery Time	trr	T_J=25℃, I_F=5A,di/dt=100A/us	-	220	-	nS
Body Diode Reverse Recovery Charge	Qrr		-	1.0	-	uC

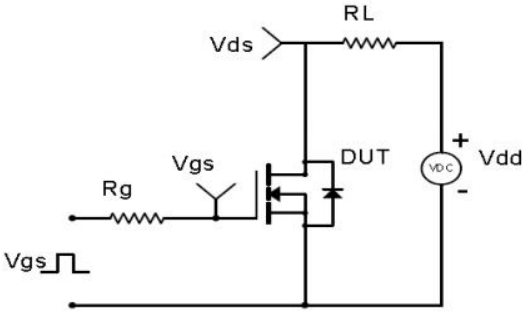
Test Circuit & Waveform

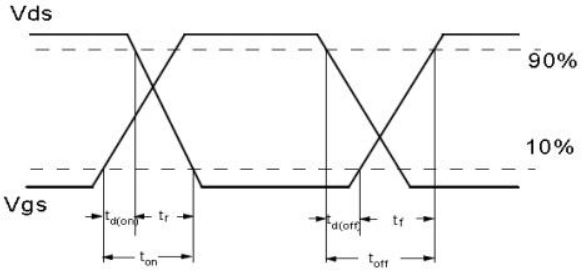
Gate Charge Test Circuit & Waveform



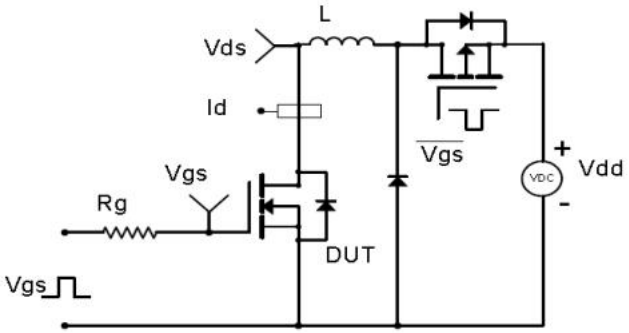


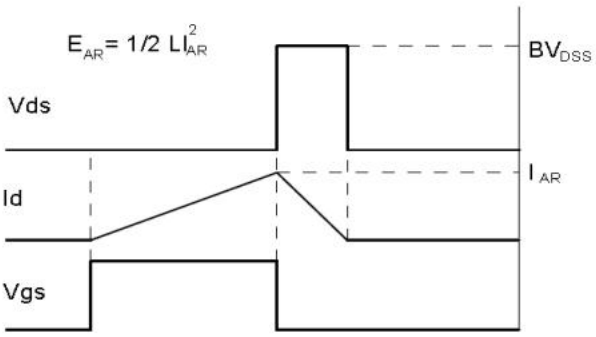
Resistive Switching Test Circuit & Waveforms



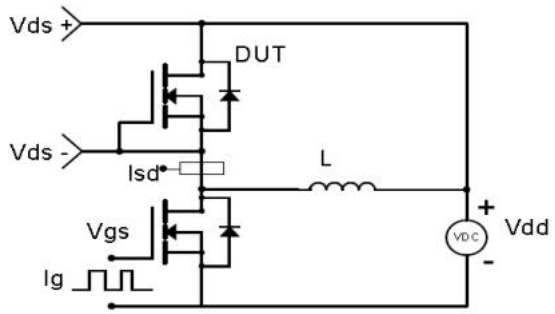


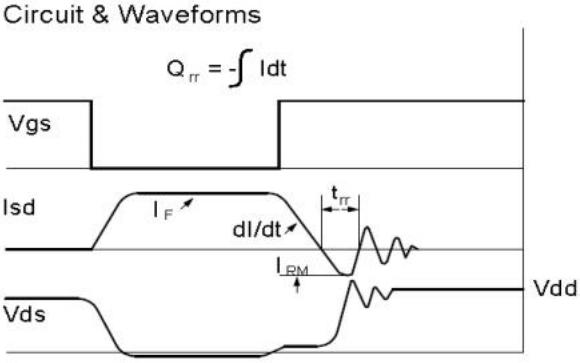
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms





Typical Characteristics

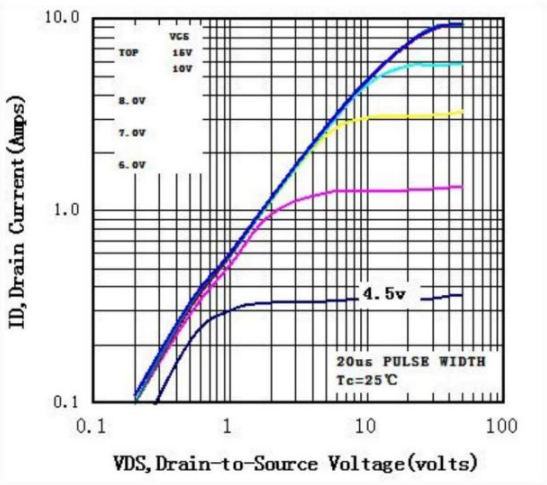


Fig1 Typical Output Characteristics, Tc=25℃

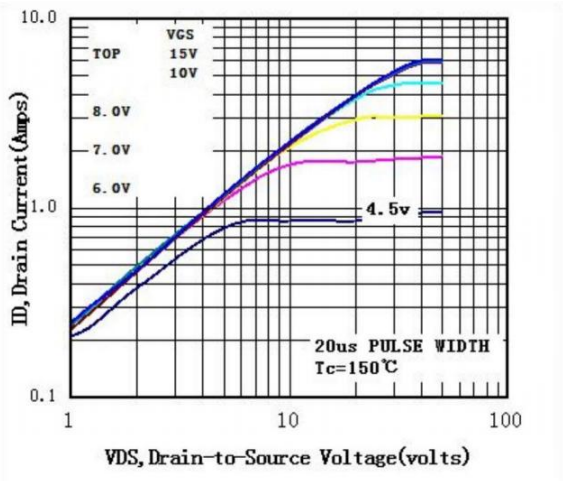


Fig2 Typical Output Characteristics, Tc=150℃

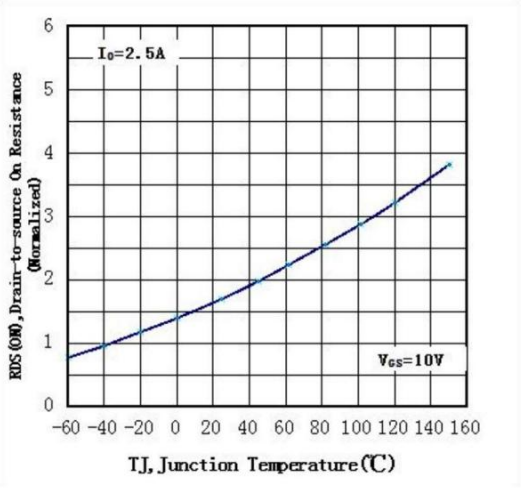


Fig3 Normalized Resistance Vs.Temperature

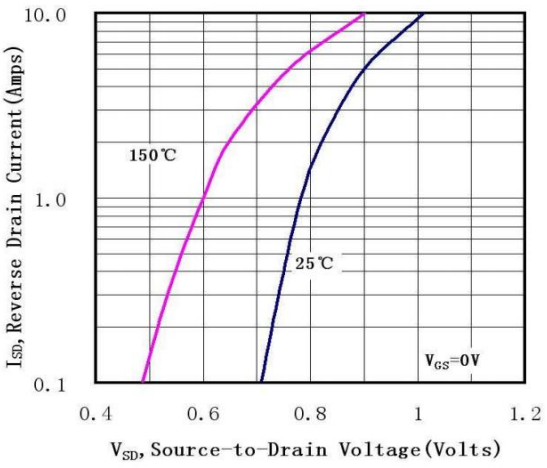


Fig4 Typical Source-Drain Diode Forward Voltage

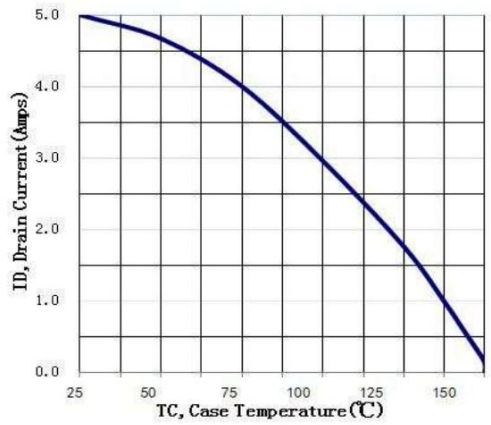


Fig5 Maximum Drain Current Vs.Case Temperature

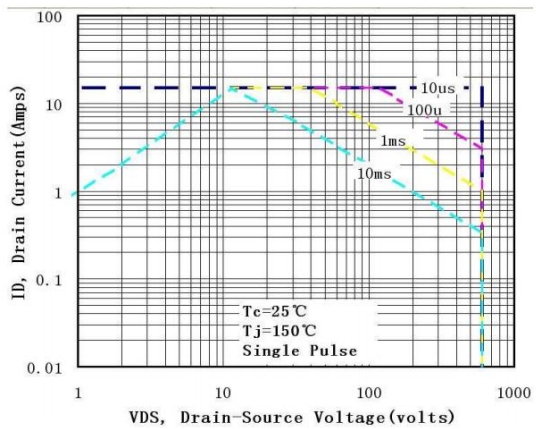
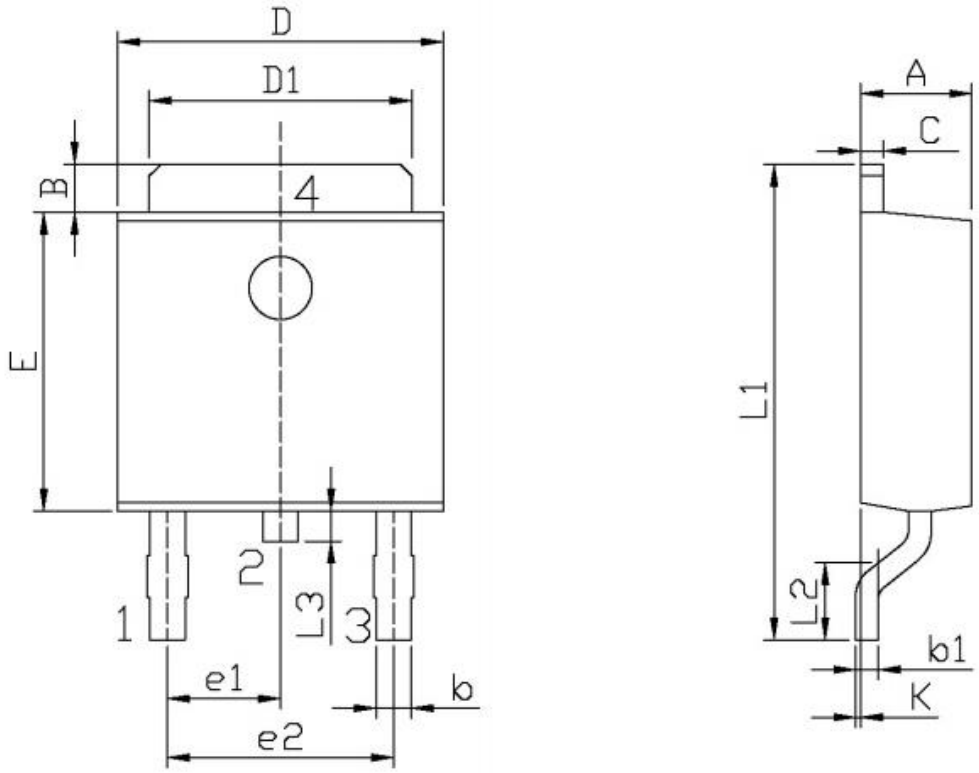


Fig6 Maximum Safe Operating Area

TO-252 Package Information



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

Revision History

Revision	Release	Remark
V1.0	2024/05/27	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product,but similar performance is not guaranteed under other working conditions,and cannot be guaranteed when installed with other products or equipment.To achieve the required performance of the product in actual scenarios,the customer should conduct a complete application test to assess the functionality of the product.

Allpower assumes no responsibility for equipment failures result from using products at values that exceed the ratings,operating conditions,or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which
requires high reliability.Customers using or selling these products for use in medical,life-saving,or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements,the information described or contained herein may be changed without prior notice.